

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

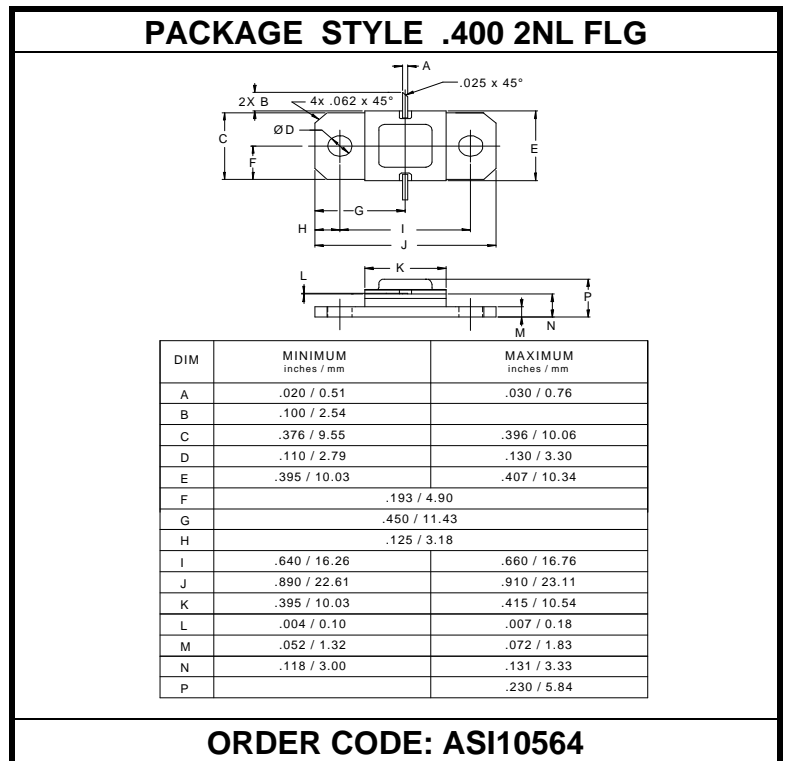
The **ASI AVD10** is Designed for

FEATURES:

- Input Matching Network
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	11 A
V_{CC}	55 V
P_{DISS}	400 W @ T _C = 25 °C
T_J	-65 °C to +250 °C
T_{STG}	-65 °C to +200 °C
θ_{JC}	0.3 °C/W


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 10 mA	65			V
BV_{CER}	I _C = 15 mA R _{BE} = 10 Ω	65			V
BV_{EBO}	I _E = 1 mA	3.5			V
I_{CES}	V _{CE} = 50 V			12.5	mA
h_{FE}	V _{CE} = 5.0 V I _C = 1.0 A	15		120	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			80	pF
P_G	V _{CC} = 50 V P _{OUT} = 150 W f = 1025 - 1150 MHz	7.7			dB
η_c		40			%